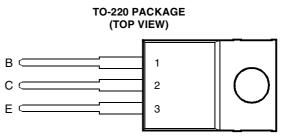
BOURNS®

BD544, BD544A, BD544B, BD544C PNP SILICON POWER TRANSISTORS

- Designed for Complementary Use with the BD543 Series
- 70 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- 10 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD544		-40		
Collector-base voltage ($I_E = 0$)	BD544A	N/	-60	v	
	BD544B	V _{CBO}	-80	v	
	BD544C		-100		
Collector-emitter voltage (I _B = 0)	BD544		-40		
	BD544A	N/	-60	V	
	BD544B	V _{CEO}	-80		
	BD544C		-100		
Emitter-base voltage	V _{EBO}	-5	V		
Continuous collector current			-8	Α	
Peak collector current (see Note 1)			-10	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			70	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Operating free air temperature range			-65 to +150	°C	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			260	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

BD544, BD544A, BD544B, BD544C PNP SILICON POWER TRANSISTORS



electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITION	ONS	MIN	ТҮР	MAX	UNIT
	Collector-emitter breakdown voltage	(see Note 4)		BD544	-40			
V _{(BR)CEO}			I _B = 0	BD544A	-60			V
				BD544B	-80			
				BD544C	-100			
	Collector-emitter	$V_{CE} = -40 V$	$V_{BE} = 0$	BD544			-0.4	mA
1070		V _{CE} = -60 V	$V_{BE} = 0$	BD544A			-0.4	
ICES	cut-off current	V _{CE} = -80 V	$V_{BE} = 0$	BD544B			-0.4	110.0
		V _{CE} = -100 V	$V_{BE} = 0$	BD544C			-0.4	
1	Collector cut-off	$V_{CE} = -30 V$	I _B = 0	BD544/544A			-0.7	mA
ICEO	current	V _{CE} = -60 V	I _B = 0	BD544B/544C			-0.7	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0				-1	mA
	Forward current transfer ratio	$V_{CE} = -4 V$	I _C = -1 A		60			
h _{FE}		$V_{CE} = -4 V$	I _C = -3 A	(see Notes 4 and 5)	40			
		$V_{CE} = -4 V$	I _C = -5 A		15			
	Collector-emitter	I _B = -0.3 A	I _C = -3 A				-0.5	
V _{CE(sat)}	saturation voltage	$l_{\rm p} = -1$ A $l_{\rm o} = -5$ A (see Notes 4 and 5)			-0.5	V		
. ,		I _B = -1.6 A	I _C = - 8A				-1	
V _{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -5 A	(see Notes 4 and 5)			-1.4	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 MHz	3			

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R_{\thetaJC}	Junction to case thermal resistance			1.79	°C/W
R_{\thetaJA}	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{or}	Turn-on time	I _C = -6 A	I _{B(on)} = -0.6 A	$I_{B(off)} = 0.6 A$		0.4		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4 V$	$R_L = 5 \Omega$	t_p = 20 µs, dc ≤ 2%		0.7		μs

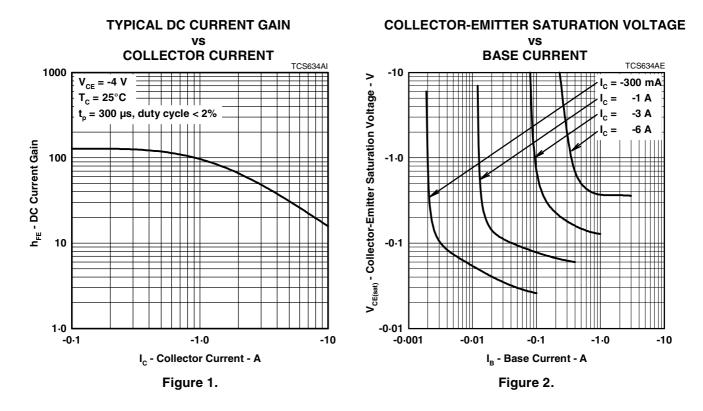
[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.





BD544, BD544A, BD544B, BD544C PNP SILICON POWER TRANSISTORS

TYPICAL CHARACTERISTICS



BASE-EMITTER VOLTAGE vs **COLLECTOR CURRENT** TCS634AF -1.2 $V_{CE} = -4 V$ T_c = 25°C -1.1 V_{BE} - Base-Emitter Voltage - V -1.0 -0.9 -0.8 -0.7 -0.6 -0.1 -1.0 -10 I_c - Collector Current - A Figure 3.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS

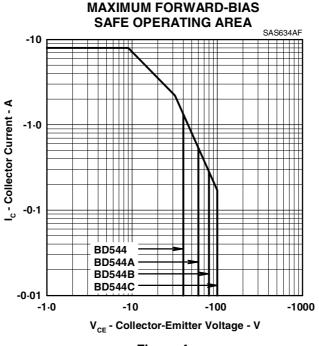
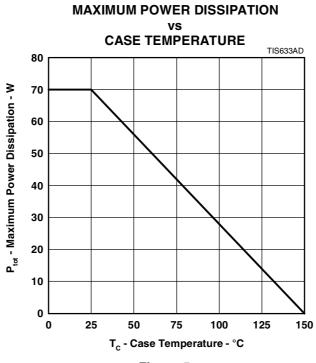


Figure 4.







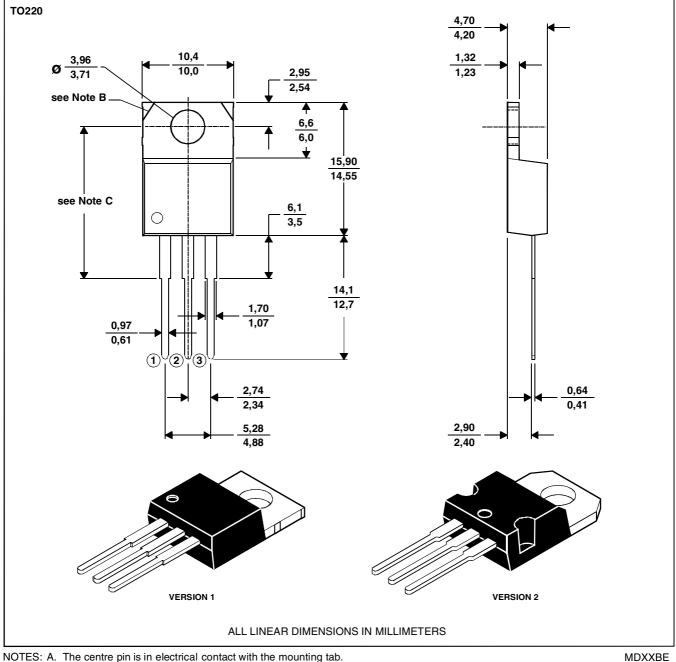
PRODUCT INFORMATION

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.